Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

Ordering number : ENA1259A

ECH8662

N-Channel Power MOSFET
40V, 6.5A, 30mΩ, Dual ECH8

ON Semiconductor®

http://onsemi.com

Features

- Low ON-resistance
- 2.5V drive
- Halogen free compliance
- Protection diode in

Specifications

Absolute Maximum Ratings at Ta=25°C

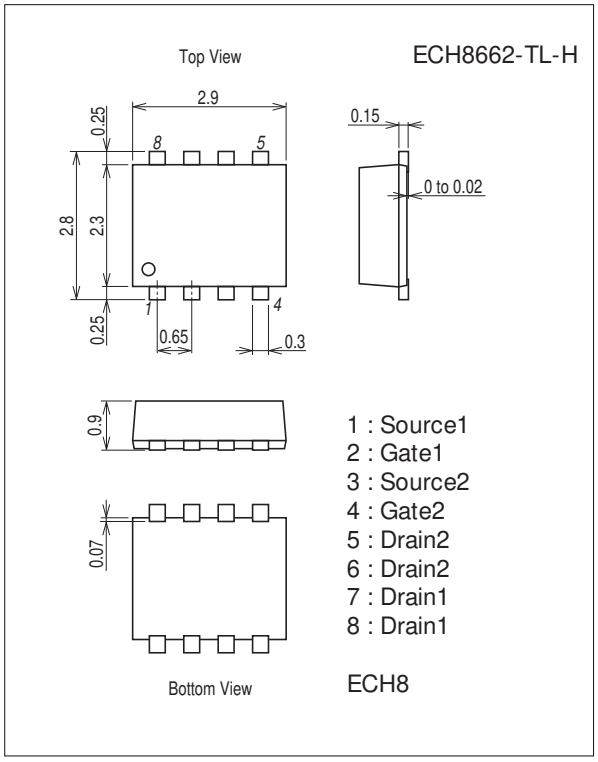
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		40	V
Gate-to-Source Voltage	V_{GSS}		±10	V
Drain Current (DC)	I_D		6.5	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	40	A
Allowable Power Dissipation	P_D	When mounted on ceramic substrate (900mm²×0.8mm) 1unit	1.3	W
Total Dissipation	P_T	When mounted on ceramic substrate (900mm²×0.8mm)	1.5	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ)

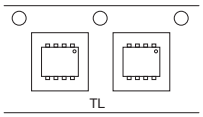
7011A-001



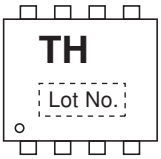
Product & Package Information

- Package : ECH8
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

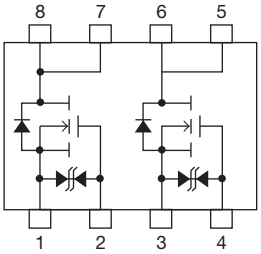
Packing Type : TL



Marking



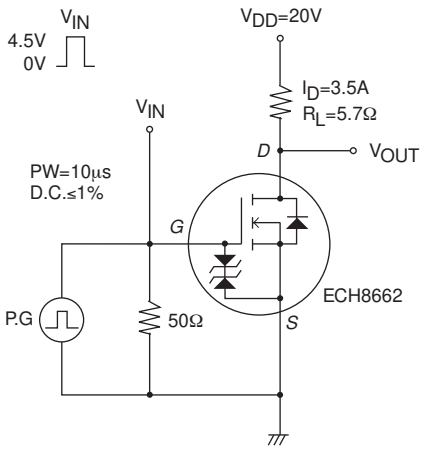
Electrical Connection



Electrical Characteristics at Ta=25°C

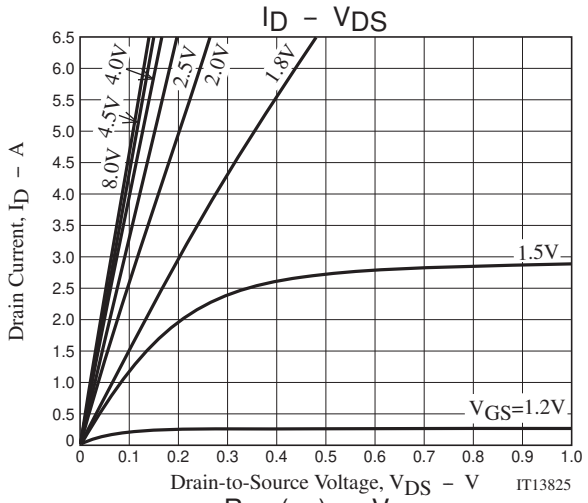
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0V	40			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=40V, V_{GS}=0V			1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0V			±10	μA
Cutoff Voltage	V_{GS}(off)	V_{DS}=10V, I_D=1mA	0.4		1.3	V
Forward Transfer Admittance	| yfs |	V_{DS}=10V, I_D=3.5A	3.9	6.5		S
Static Drain-to-Source On-State Resistance	R_{DS}(on)1	I_D=3.5A, V_{GS}=4.5V		23	30	mΩ
	R_{DS}(on)2	I_D=3.5A, V_{GS}=4V		25	33	mΩ
	R_{DS}(on)3	I_D=1.5A, V_{GS}=2.5V		30	42	mΩ
Input Capacitance	Ciss	V_{DS}=20V, f=1MHz		1130		pF
Output Capacitance	Coss	V_{DS}=20V, f=1MHz		77		pF
Reverse Transfer Capacitance	Crss	V_{DS}=20V, f=1MHz		60		pF
Turn-ON Delay Time	t_d(on)	See specified Test Circuit.		14		ns
Rise Time	t_r			34		ns
Turn-OFF Delay Time	t_d(off)			93		ns
Fall Time	t_f			55		ns
Total Gate Charge	Qg	V_{DS}=20V, V_{GS}=4.5V, I_D=6.5A		12		nC
Gate-to-Source Charge	Qgs			2.2		nC
Gate-to-Drain "Miller" Charge	Qgd			3.4		nC
Diode Forward Voltage	V_{SD}	I_S=6.5A, V_{GS}=0V		0.85	1.2	V

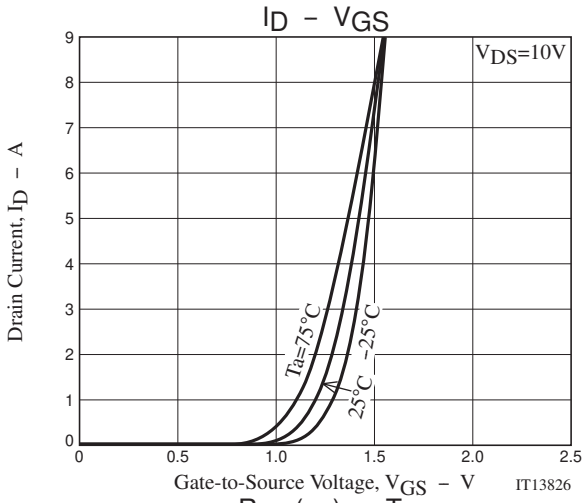
Switching Time Test Circuit

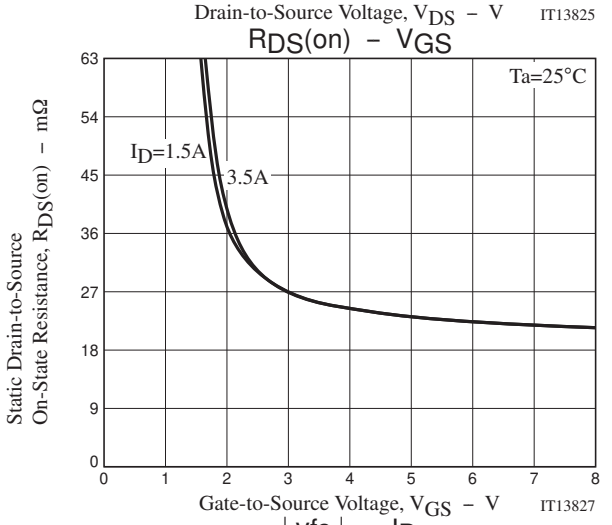


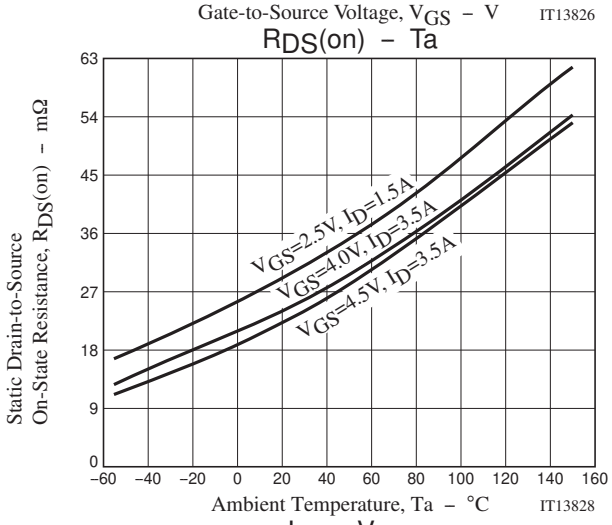
Ordering Information

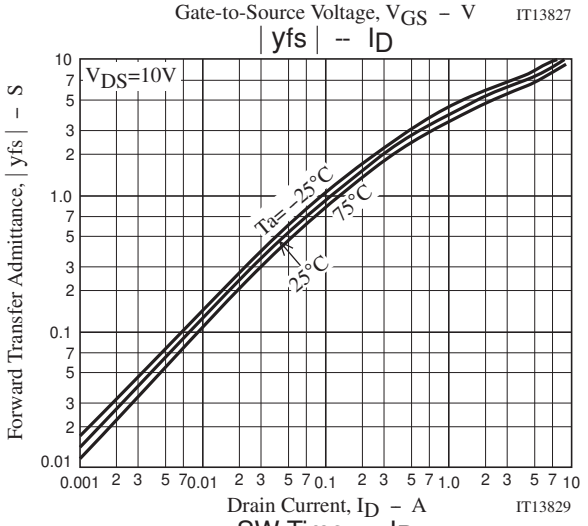
Device	Package	Shipping	memo
ECH8662-TL-H	ECH8	3,000pcs./reel	Pb Free and Halogen Free

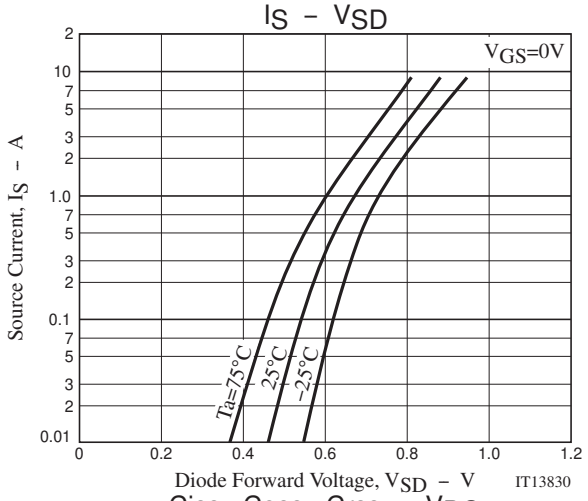

ID – VDS
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT13825
8.0V
4.5V
4.0V
2.5V
2.0V
1.8V
1.5V
VGS=1.2V

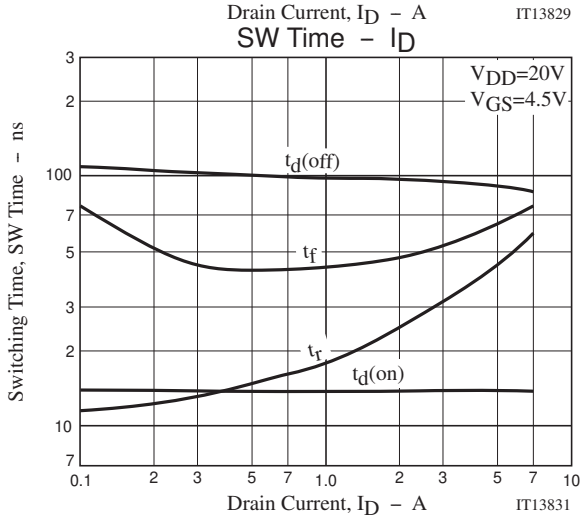

ID – VGS
VDS=10V
Drain Current, ID – A
Gate-to-Source Voltage, VGS – V
IT13826
Ta=75°C
25°C
–25°C

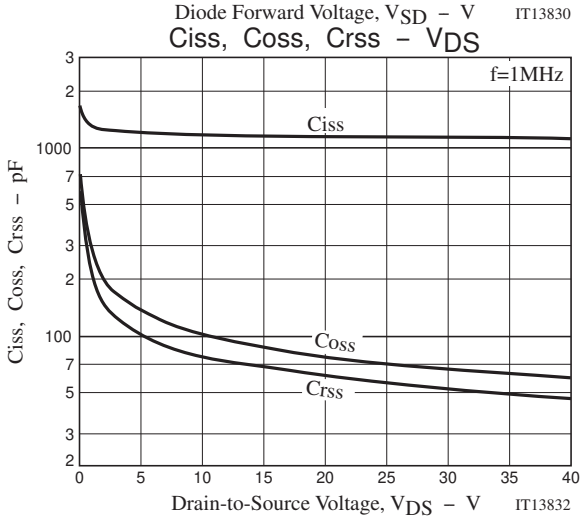

RDS(on) – VGS
Ta=25°C
ID=1.5A
3.5A
Static Drain-to-Source
On-State Resistance, RDS(on) – mΩ
Gate-to-Source Voltage, VGS – V
IT13827

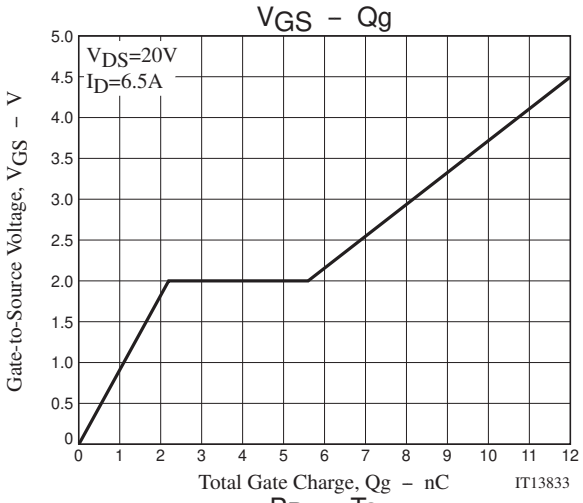

RDS(on) – Ta
VGS=2.5V, ID=1.5A
VGS=4.0V, ID=3.5A
VGS=4.5V, ID=3.5A
Static Drain-to-Source
On-State Resistance, RDS(on) – mΩ
Ambient Temperature, Ta – °C
IT13828

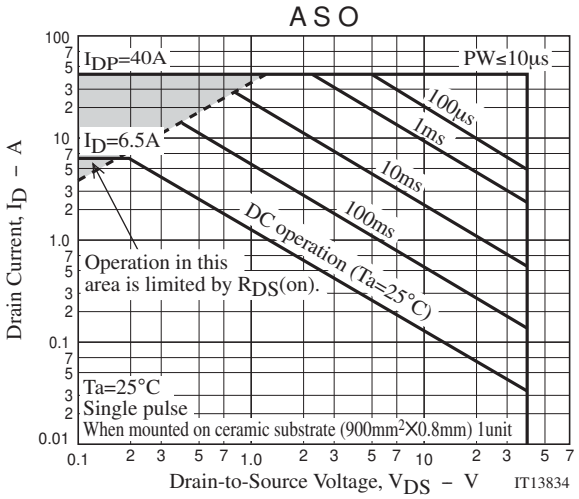

| yfs | – ID
VDS=10V
Ta= –25°C
75°C
25°C
Forward Transfer Admittance, | yfs | – S
Drain Current, ID – A
IT13829

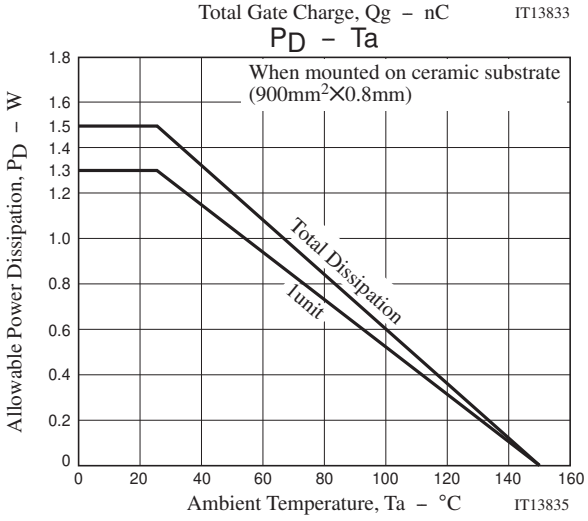

IS – VSD
VGS=0V
Ta=75°C
25°C
–25°C
Source Current, IS – A
Diode Forward Voltage, VSD – V
IT13830


SW Time – ID
VDD=20V
VGS=4.5V
td(off)
tf
tr
td(on)
Switching Time, SW Time – ns
Drain Current, ID – A
IT13831


Ciss, Coss, Crss – VDS
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS – V
IT13832


VGS – Qg
VDS=20V
ID=6.5A
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT13833


A S O
IDP=40A
PW≤10μs
ID=6.5A
100μs
1ms
10ms
100ms
DC operation (Ta=25°C)
Operation in this
area is limited by RDS(on).
Ta=25°C
Single pulse
When mounted on ceramic substrate (900mm2×0.8mm) 1unit
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT13834


PD – Ta
When mounted on ceramic substrate
(900mm2×0.8mm)
Total Dissipation
1unit
Allowable Power Dissipation, PD – W
Ambient Temperature, Ta – °C
IT13835

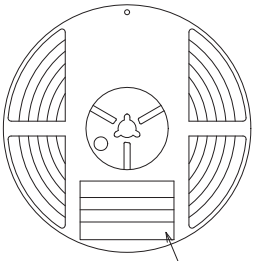
Embossed Taping Specification

ECH8662-TL-H

1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
ECH8	CPH6	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

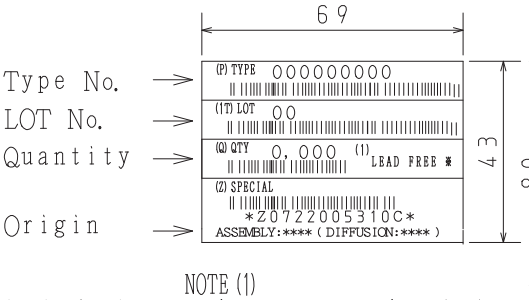
Packing method



Reel label

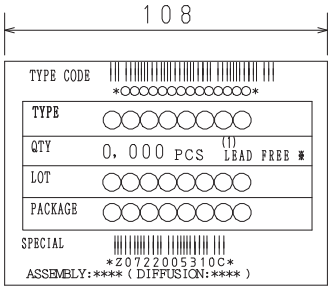
Reel label, Inner box label

(unit:mm)



Outer box label

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.

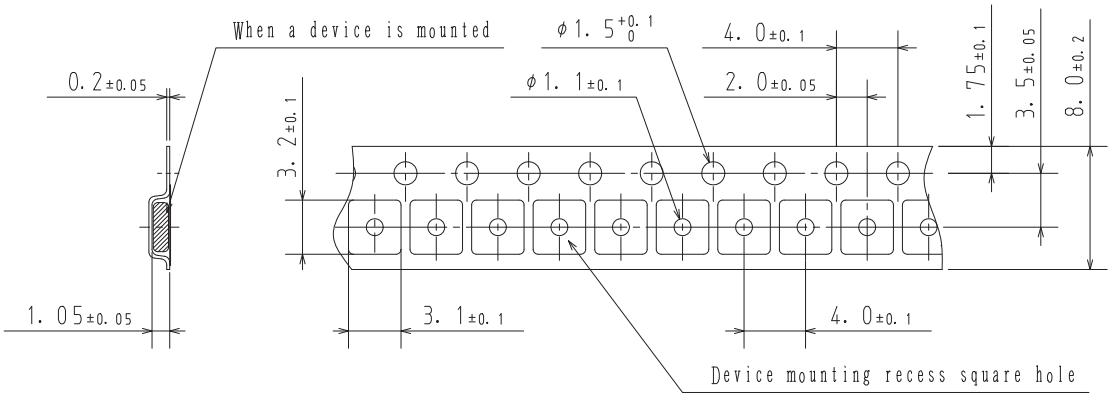


NOTE (1)
The LEAD FREE ※ description shows that the surface treatment of the terminal is lead free.

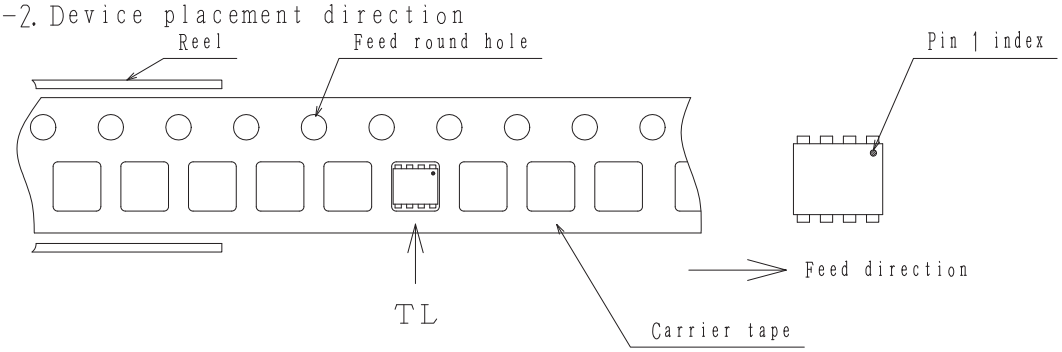
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



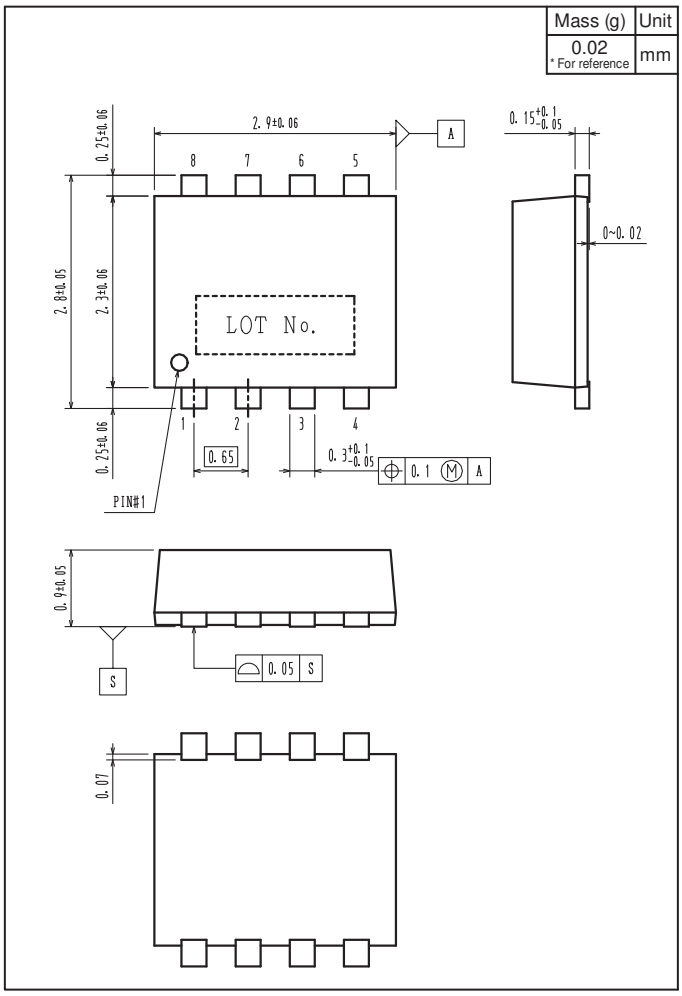
2-2. Device placement direction



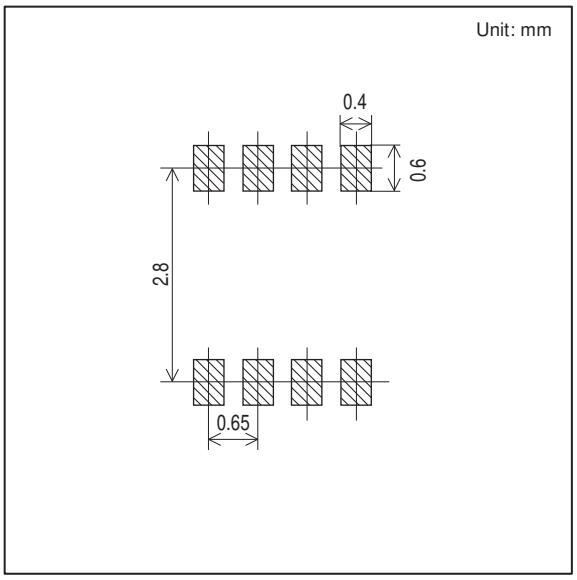
Those with pin 1 index on the feed hole side·····TL

Outline Drawing

ECH8662-TL-H



Land Pattern Example



Note on usage : Since the ECH8662 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.